

PMEG2020EH

20 V, 2 A very low V_F MEGA Schottky barrier rectifier in SOD123F package

Rev. 02 — 23 May 2005

Product data sheet



1. Product profile

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection encapsulated in a SOD123F small SMD plastic package.

1.2 Features

Forward current: 2 A

Reverse voltage: 20 V

- Very low forward voltage
- Small and flat lead SMD package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Inverse polarity protection
- Low power consumption applications

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _F	forward current	T _{sp} ≤ 55 °C	-	-	2	Α
V_R	reverse voltage		-	-	20	V
V _F	forward voltage	I _F = 2 A	[1] -	450	525	mV

[1] Pulse test: $t_0 \le 300 \,\mu\text{s}$; $\delta \le 0.02$.



2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	cathode	[1]	. 54
2	anode	1 2	1 🔁 2
			sym001

^[1] The marking bar indicates the cathode.

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PMEG2020EH	-	plastic surface mounted package; 2 leads	SOD123F

4. Marking

Table 4: Marking codes

Type number	Marking code
PMEG2020EH	A6

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_R	reverse voltage		-	20	V
l _F	forward current	T _{sp} ≤ 55 °C	-	2	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.5$	-	7	Α
I _{FSM}	non-repetitive peak forward current	t = 8 ms; square wave	-	9	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u> _	375	mW
			[2] _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

9397 750 15081

 $[\]label{eq:continuous} \ensuremath{\text{[2]}} \quad \text{Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm2.}$

6. Thermal characteristics

Table 6: Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	330	K/W
			[1][3]	-	150	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	60	K/W

^[1] For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and I_{F(AV)} rating will be available on request.

7. Characteristics

Table 7: Characteristics

T_{amb} = 25 °C unless otherwise specified.

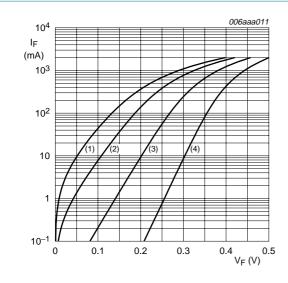
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _F	forward voltage		<u>[1]</u>			
		I _F = 0.01 A	-	200	220	mV
		I _F = 0.1 A	-	260	290	mV
		I _F = 1 A	-	370	430	mV
		I _F = 2 A	-	450	525	mV
I _R	reverse current		[2]			
		V _R = 5 V	-	15	50	μΑ
		V _R = 10 V	-	20	80	μΑ
		V _R = 20 V	-	45	200	μΑ
C _d	diode capacitance	$V_R = 5 V; f = 1 MHz$	-	50	60	pF

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

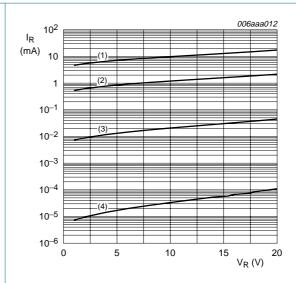
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

^[2] For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.



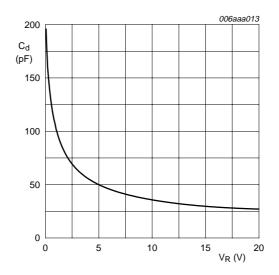
- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \,^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

Fig 1. Forward current as a function of forward voltage; typical values



- (1) $T_{amb} = 125 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

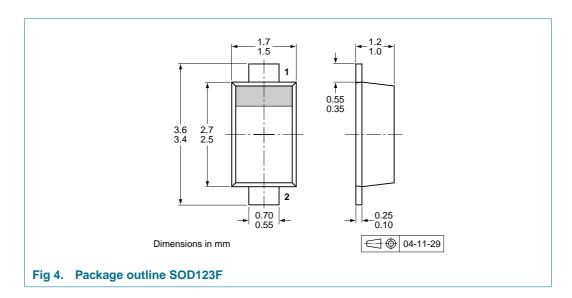
Fig 2. Reverse current as a function of reverse voltage; typical values



 T_{amb} = 25 °C; f = 1 MHz

Fig 3. Diode capacitance as a function of reverse voltage; typical values

8. Package outline



9. Packing information

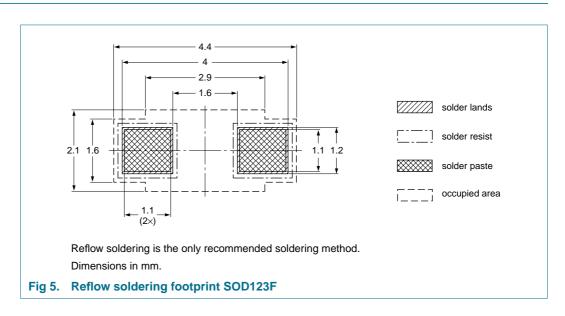
Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number	Package	Description	Packing quantity
			3000
PMEG2020EH	SOD123F	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see $\underline{\text{Section 16}}$.

10. Soldering



9397 750 15081

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11. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PMEG2020EH_2	20050523	Product data sheet	-	9397 750 15081	PMEG2020EH_1
Modifications:	• Table 5 "Li	miting values" IFSM value	changed to 9 A		
PMEG2020EH_1	20050304	Preliminary data sheet	-	9397 750 14518	-

12. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- [3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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PMEG2020EH

20 V, 2 A very low V_F MEGA Schottky barrier rectifier

17. Contents

1	Product profile
1.1	General description 1
1.2	Features
1.3	Applications
1.4	Quick reference data1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values
6	Thermal characteristics 3
7	Characteristics 3
8	Package outline 5
9	Packing information 5
10	Soldering 5
11	Revision history 6
12	Data sheet status
13	Definitions 7
14	Disclaimers 7
15	Trademarks 7
16	Contact information 7



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